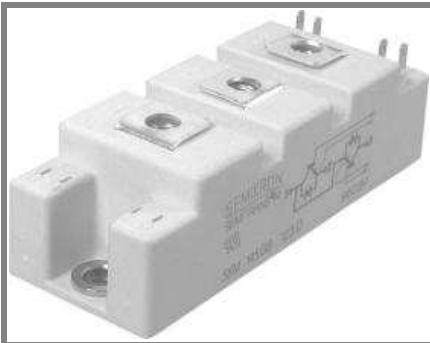


SKM 75GB063D



SEMITRANS[®] 2

Superfast NPT-IGBT Modules

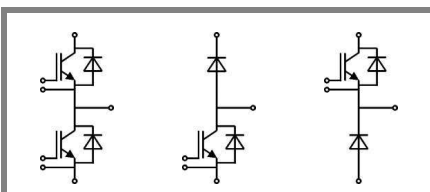
SKM 75GB063D
SKM 75GAR063D
SKM 75GAL063D

Features

- N channel, homogeneous Si-structure (NPT-Non punch-through IGBT)
- Low tail current with low temperature dependence
- High short circuit capability, self limiting if term. G is clamped to E
- Pos. temp.-coeff. of V_{CEsat}
- Very low C_{ies} , C_{oes} , C_{res}
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DBC Direct Copper Bonding Technology without hard mould
- Large clearance (10 mm) and creepage distances (20 mm)

Typical Applications*

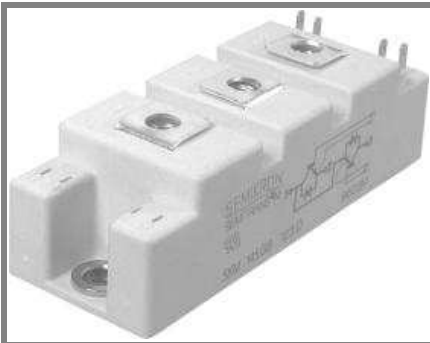
- Switching (not for linear use)
- Switched mode power supplies
- UPS
- Three phase inverters for servo / AC motor speed control
- Pulse frequencies also > 10kHz



GB GAL GAR

Absolute Maximum Ratings		$T_c = 25\text{ }^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	Values		Units	
IGBT					
V_{CES}	$T_j = 25\text{ }^\circ\text{C}$	600		V	
I_C	$T_j = 150\text{ }^\circ\text{C}$	$T_{case} = 25\text{ }^\circ\text{C}$	100	A	
		$T_{case} = 75\text{ }^\circ\text{C}$	75	A	
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	150		A	
V_{GES}		± 20		V	
t_{psc}	$V_{CC} = 300\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ }^\circ\text{C}$ $V_{CES} < 600\text{ V}$	10		μs	
Inverse Diode					
I_F	$T_j = 150\text{ }^\circ\text{C}$	$T_{case} = 25\text{ }^\circ\text{C}$	75	A	
		$T_{case} = 80\text{ }^\circ\text{C}$	50	A	
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	150		A	
I_{FSM}	$t_p = 10\text{ ms}; \sin.$	$T_j = 150\text{ }^\circ\text{C}$	440		A
Freewheeling Diode					
I_F	$T_j = 150\text{ }^\circ\text{C}$	$T_c = 25\text{ }^\circ\text{C}$	100	A	
		$T_c = 80\text{ }^\circ\text{C}$	75	A	
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	200		A	
I_{FSM}	$t_p = 10\text{ ms}; \sin$	$T_j = 150\text{ }^\circ\text{C}$	720		A
Module					
$I_{t(RMS)}$		200		A	
T_{vj}		- 40 ... + 150		$^\circ\text{C}$	
T_{stg}		- 40 ... + 125		$^\circ\text{C}$	
V_{isol}	AC, 1 min.	2500		V	

Characteristics		$T_c = 25\text{ }^\circ\text{C}$, unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1\text{ mA}$	4,5	5,5	6,5	V	
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$		$T_j = 25\text{ }^\circ\text{C}$ 0,1	0,3	$T_j = 125\text{ }^\circ\text{C}$ mA	
V_{CE0}			$T_j = 25\text{ }^\circ\text{C}$	1,05	V	
			$T_j = 125\text{ }^\circ\text{C}$	1	V	
r_{CE}	$V_{GE} = 15\text{ V}$		$T_j = 25\text{ }^\circ\text{C}$	14	$\text{m}\Omega$	
			$T_j = 125\text{ }^\circ\text{C}$	18,7	$\text{m}\Omega$	
$V_{CE(sat)}$	$I_{Cnom} = 75\text{ A}, V_{GE} = 15\text{ V}$		$T_j = 25\text{ }^\circ\text{C}_{chiplev.}$	2,1	2,5	V
			$T_j = 125\text{ }^\circ\text{C}_{chiplev.}$	2,4	2,8	V
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$		4,2	nF	
C_{oes}			0,5	nF		
C_{res}			0,3	nF		
Q_G	$V_{GE} = 0\text{ V} \dots +15\text{ V}$		180		nC	
R_{Gint}	$T_j = \text{ }^\circ\text{C}$		0		Ω	
$t_{d(on)}$	$R_{Gon} = 15\text{ } \Omega$	$V_{CC} = 300\text{ V}$ $I_C = 75\text{ A}$		60	ns	
t_r				50	ns	
E_{on}				3	mJ	
$t_{d(off)}$	$R_{Goff} = 15\text{ } \Omega$	$T_j = 125\text{ }^\circ\text{C}$ $V_{GE} = \pm 15\text{ V}$		350	ns	
t_f				35	ns	
E_{off}				2,5	mJ	
$R_{th(j-c)}$	per IGBT			0,35	K/W	



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Superfast NPT-IGBT Modules

SKM 75GB063D

SKM 75GAR063D

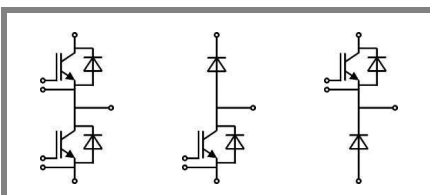
SKM 75GAL063D

Features

- N channel, homogeneous Si-structure (NPT-Non punch-through IGBT)
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- High short circuit capability, self limiting if term. G is clamped to E
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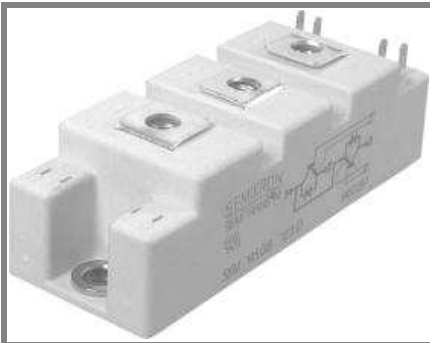
GAR

Characteristics			min.	typ.	max.	Units
Inverse Diode						
$V_F = V_{EC}$	$I_{Fnom} = 75 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$		1,55	1,9	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$		1,55		V
V_{F0}		$T_j = 125 \text{ }^\circ\text{C}$			0,9	V
r_F		$T_j = 125 \text{ }^\circ\text{C}$		10	13,3	m Ω
I_{RRM}	$I_F = 75 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$		30		A
Q_{rr}	$di/dt = 800 \text{ A}/\mu\text{s}$			3,7		μC
E_{rr}	$V_{GE} = -15 \text{ V}; V_{CC} = 300 \text{ V}$					mJ
$R_{th(j-c)D}$	per diode				0,72	K/W
Freewheeling Diode						
$V_F = V_{EC}$	$I_{Fnom} = 100 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$		1,55	1,9	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$		1,55		V
V_{F0}		$T_j = 125 \text{ }^\circ\text{C}$			0,9	V
r_F		$T_j = 125 \text{ }^\circ\text{C}$		8	10	V
I_{RRM}	$I_F = 100 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$		44		A
Q_{rr}	$di/dt = 0 \text{ A}/\mu\text{s}$			6		μC
E_{rr}	$V_{GE} = -15 \text{ V}; V_{CC} = 300 \text{ V}$					mJ
$R_{th(j-c)FD}$	per diode				0,6	K/W
Module						
L_{CE}					30	nH
$R_{CC+EE'}$	res., terminal-chip	$T_{case} = 25 \text{ }^\circ\text{C}$		0,75		m Ω
		$T_{case} = 125 \text{ }^\circ\text{C}$		1		m Ω
$R_{th(c-s)}$	per module				0,05	K/W
M_s	to heat sink M6			3	5	Nm
M_t	to terminals M5			2,5	5	Nm
w					160	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

SKM 75GB063D



SEMITRANS[®] 2

Superfast NPT-IGBT Modules

SKM 75GB063D

SKM 75GAR063D

SKM 75GAL063D

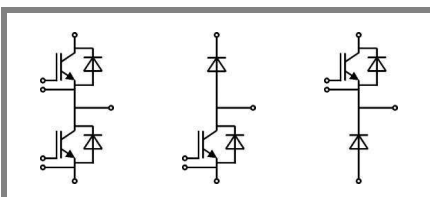
Features

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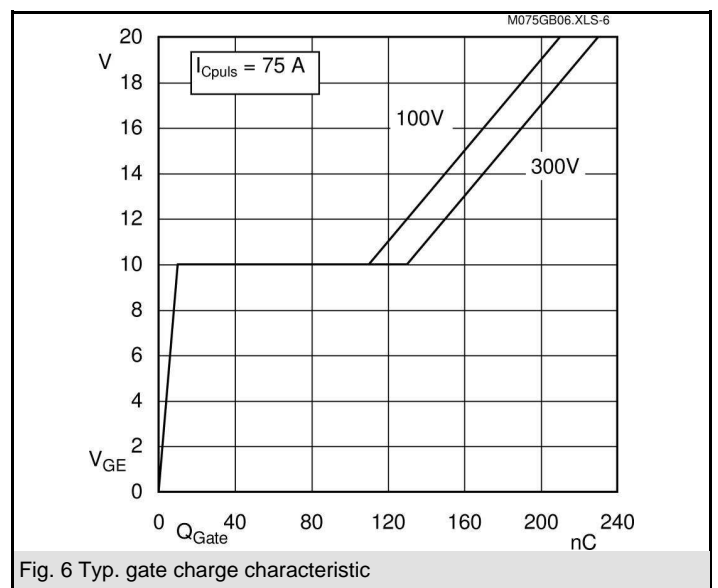
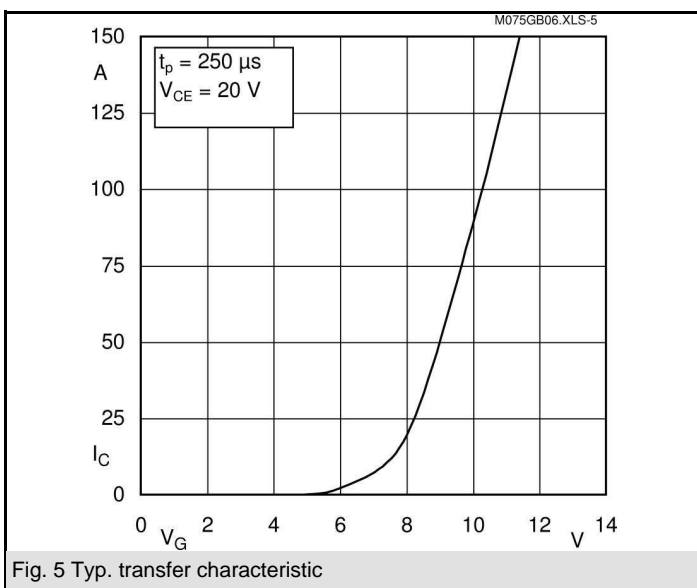
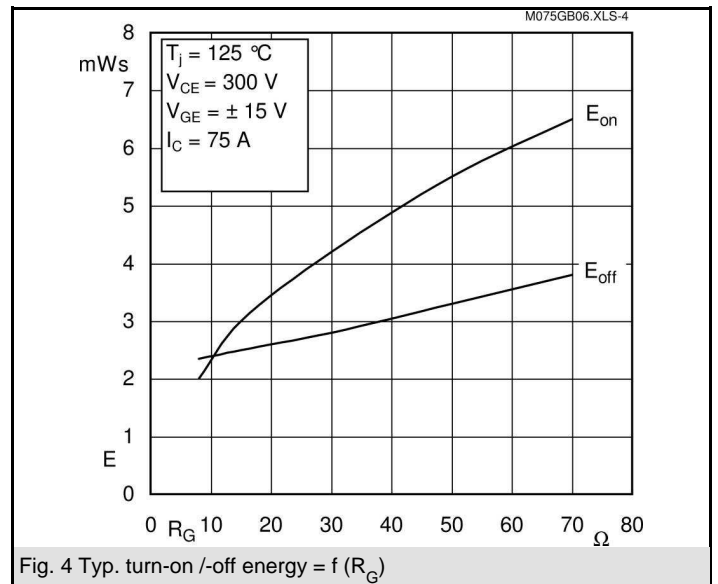
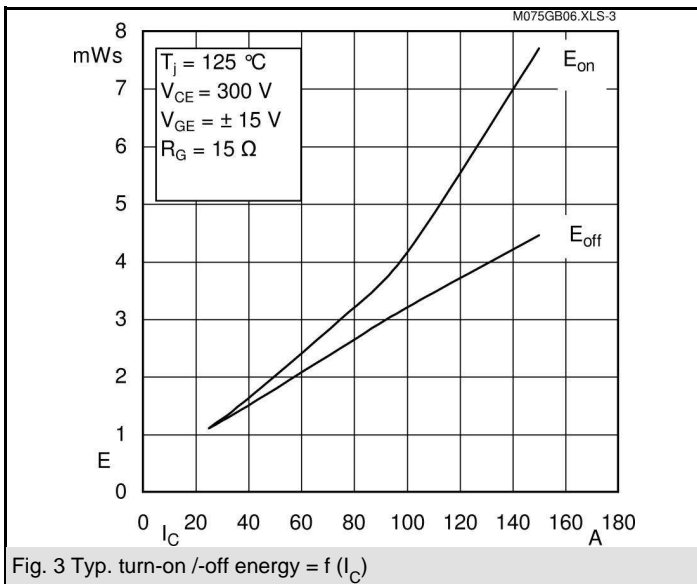
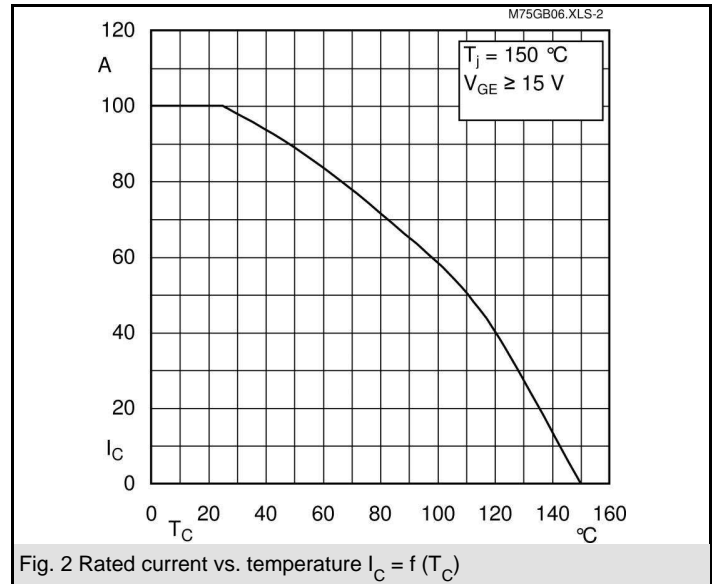
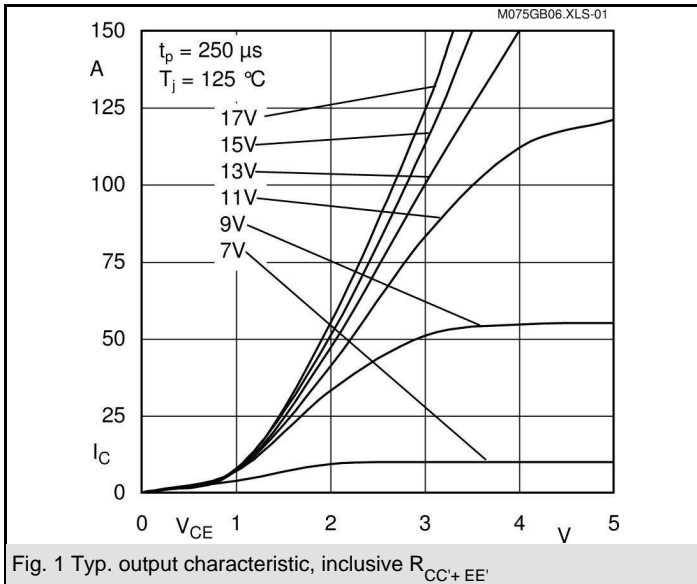
Z_{th}	Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$	$R_{\theta j-c}$	i = 1	250	mk/W
	$R_{\theta j-c}$	i = 2	70	mk/W
	$R_{\theta j-c}$	i = 3	25	mk/W
	$R_{\theta j-c}$	i = 4	5	mk/W
	$\tau_{th(j-c)}$	i = 1	0,0874	s
	$\tau_{th(j-c)}$	i = 2	0,0078	s
	$\tau_{th(j-c)}$	i = 3	0,0017	s
	$\tau_{th(j-c)}$	i = 4	0,0001	s
$Z_{th(j-c)D}$	$R_{\theta j-cD}$	i = 1	550	mk/W
	$R_{\theta j-cD}$	i = 2	340	mk/W
	$R_{\theta j-cD}$	i = 3	92	mk/W
	$R_{\theta j-cD}$	i = 4	18	mk/W
	$\tau_{th(j-c)D}$	i = 1	0,0761	s
	$\tau_{th(j-c)D}$	i = 2	0,0045	s
	$\tau_{th(j-c)D}$	i = 3	0,011	s
	$\tau_{th(j-c)D}$	i = 4	0,0002	s

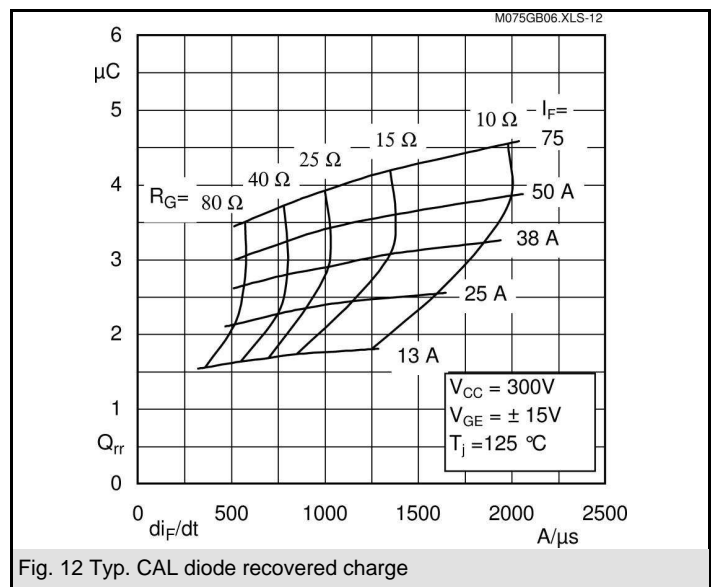
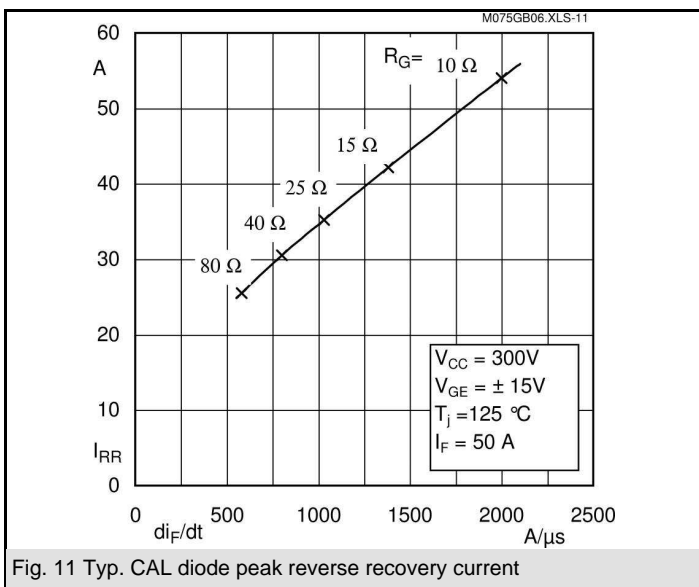
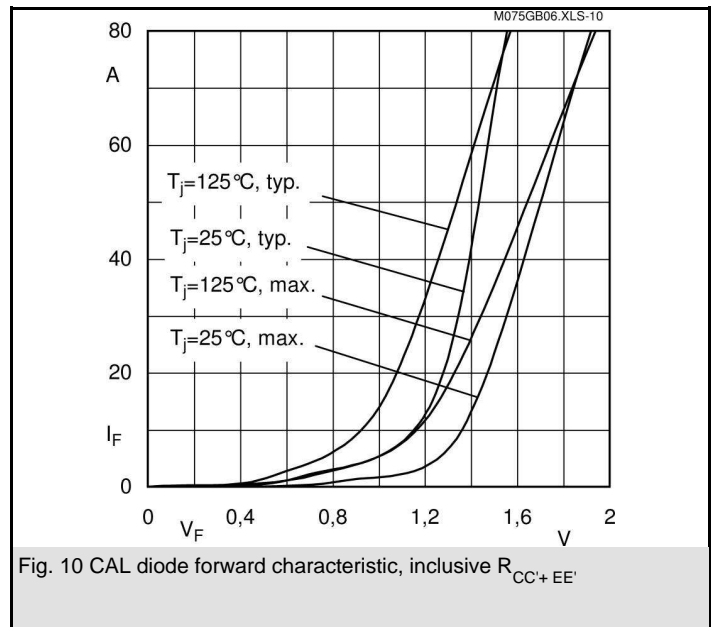
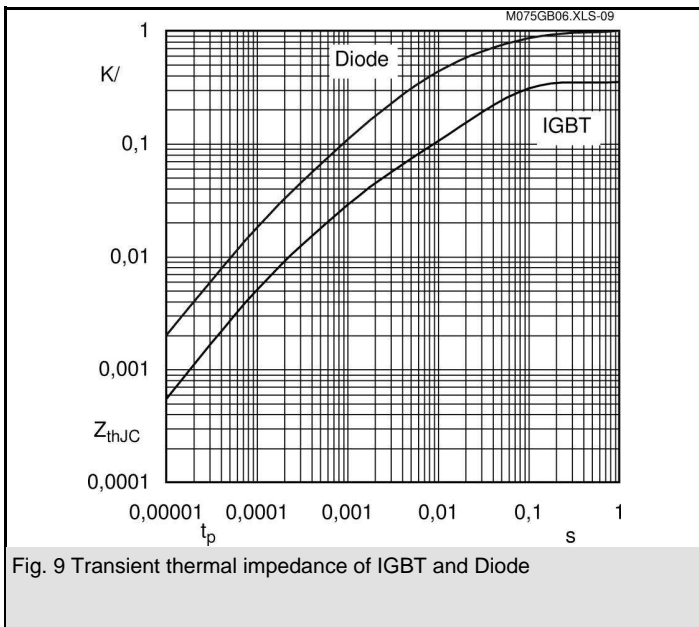
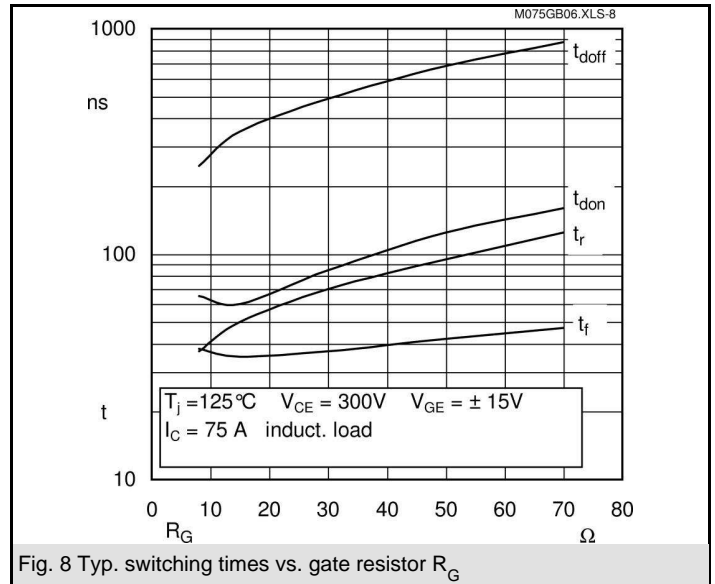
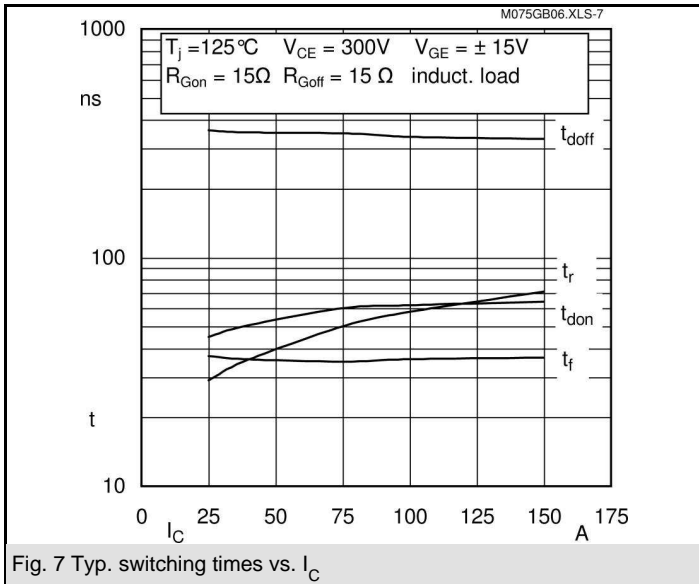


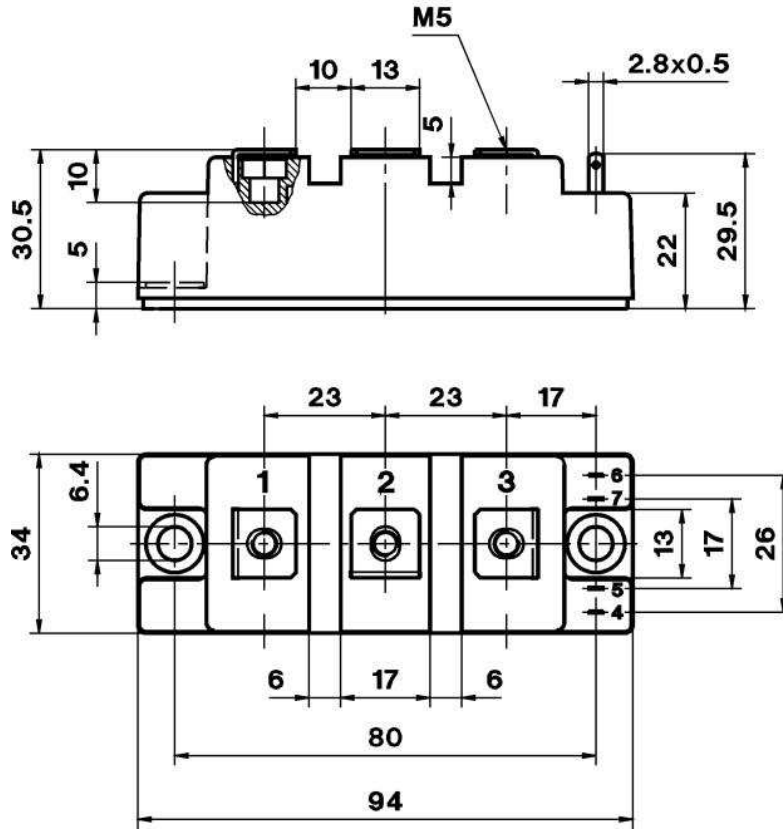
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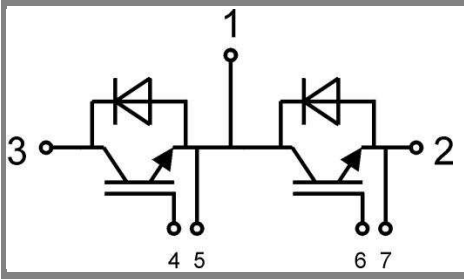
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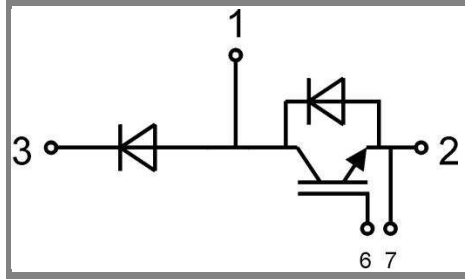




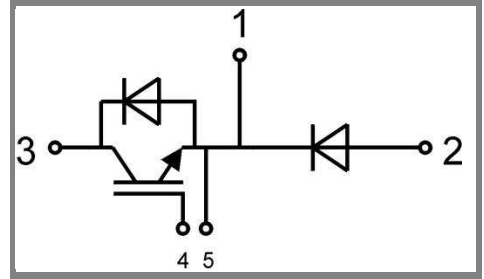
Case D 61



GB Case D 61



GAL Case D 62 (→ D 61)



GAR Case D 63 (→ D 61)